IN THE CLAIMS:

1. A method of fabricating an integrated circuit, comprising the steps of:

forming a first interlevel dielectric over a semiconductor body;

forming a layer of resistor material over said first interlevel dielectric layer;

forming a metal stack on said layer of resistor material;

forming a first pattern over said metal stack;

etching said metal stack and said layer of resistor material using said first pattern;

removing said first pattern;

forming a second pattern to expose a portion of said metal stack over a thin film resistor area;

removing said exposed portion of said metal stack to form a thin film resistor.

2. The method of claim 1, wherein said second pattern is a photoresist pattern.

3. The method of claim 1, wherein said second pattern is a hardmask.

4. The method of claim 3, wherein said step of forming said second pattern comprises the steps of:

forming a hardmask layer over said metal stack;

forming a photoresist pattern over said hardmask layer to expose a portion of said hardmask layer over the thin film resistor area.;

removing said exposed portion of said hardmask layer; and

removing said photoresist pattern.

5. The method of claim 4, wherein said hardmask layer comprises silicon dioxide.

6. The method of claim 1, wherein said interlevel dielectric layer comprises vias formed at a surface thereof.

7. The method of claim 1, wherein a portion of said metal stack remains at a first end and a second end of said thin film resistor.

8. A method of fabricating a thin film resistor in an integrated circuit, comprising the steps of:

providing a semiconductor body having a first interlevel dielectric layer;

forming a layer of resistor material over said first interlevel dielectric layer;

forming a metal stack on said layer of resistor material;

forming a first pattern over said metal stack, said first pattern covering said metal stack where a plurality of metal lines and said thin film resistor are desired;

dry etching said metal stack and said layer of resistor material using said first pattern to form said plurality of metal lines;

removing said first pattern;

forming a second pattern to expose a portion of said metal stack over a thin film resistor area;

removing said exposed portion of said metal stack using a wet etch to form said thin film resistor;

removing said second pattern; and

forming a second interlevel dielectric layer over said plurality of metal lines and said thin film resistor.

9. The method of claim 8, wherein said second pattern is a photoresist pattern.

10. The method of claim 8, wherein said second pattern is a hardmask.

11. The method of claim 10, wherein said step of forming said second pattern comprises the steps of:

forming a hardmask layer over said metal stack;

forming a photoresist pattern over said hardmask layer to expose a portion of said hardmask layer over the thin film resistor area.;

removing said exposed portion of said hardmask layer; and

removing said photoresist pattern.

12. The method of claim 8, wherein said first interlevel dielectric layer comprises vias formed at a surface thereof.

13. The method of claim 8, wherein a portion of said metal stack remains at a first end and a second end of said thin film resistor.

14. An integrated circuit, comprising:

a first interlevel dielectric layer;

a layer of resistor material located over a portion of said first interlevel dielectric layer;

a plurality of metal interconnect lines located over a first portion but not a second portion of said layer of resistor material, wherein said second portion of said layer of resistor material forms a thin film resistor.

15. The integrated circuit of claim 14, further comprising a second interlevel dielectric layer over said thin film resistor and said plurality of metal interconnect lines.

16. The integrated circuit of claim 14, wherein a portion of said plurality of metal interconnect lines is electrically connected to an end portion of said thin film resistor.